

### NOT RECOMMENDED FOR NEW DESIGN USE DMP3007SPS



## DMP3010LPS

### P-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C
-30V	$7.5 \text{m}\Omega$ @ $V_{GS} = -10V$	-36A
	$10m\Omega$ @ $V_{GS} = -4.5V$	-31A

### **Description**

This new generation 30V P-Channel Enhancement Mode MOSFET is designed to minimize R<sub>DS(ON)</sub>, yet maintain superior switching performance. This device is ideal for use in notebook battery power management and loadswitch.

PowerDI5060-8

### **Applications**

- Notebook Battery Power Management
- DC-DC Converters
- Loadswitch

### **Features**

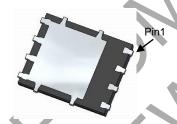
- Thermally Efficient Package Cooler Running Applications
- High Conversion Efficiency
- Low R<sub>DS(ON)</sub> Minimizes On-State Losses
- Low Input Capacitance
- Fast Switching Speed
- <1.1mm Package Profile Ideal for Thin Applications
- ESD HBM Protected up to 1kV
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2) Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (DMP3010LPSQ)

### **Mechanical Data**

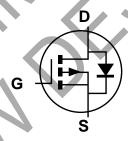
- Case: PowerDI<sup>®</sup>5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
  Terminals: Finish 100% Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.097 grams (Approximate)



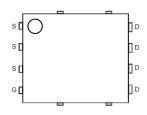
Top View



**Bottom View** 



Internal Schematic



Top View Pin Configuration

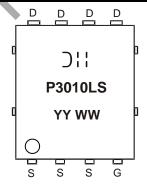
### Ordering Information (Note 4)

Part Number	Compliance	Case	Packaging
DMP3010LPS-13	Standard	PowerDI5060-8	2,500/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and 1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

### Marking Information



☐ = Manufacturer's Marking P3010LS = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 17 = 2017)WW = Week (01 to 53)



### NOT RECOMMENDED FOR NEW DESIGN **USE DMP3007SPS**

DMP3010LPS

## **Maximum Ratings** ( $@T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V <sub>DSS</sub>	-30	V		
Gate-Source Voltage	$V_{GSS}$	±20	V		
Continuous Drain Current (Note 7) V <sub>GS</sub> = -10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I <sub>D</sub>	-36 -29	А
Continuous Drain Current (Note 7) V <sub>GS</sub> = -4.5V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	ID	-31 -25	А
Continuous Drain Current (Note 6) V <sub>GS</sub> = -10V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I <sub>D</sub>	-14.5 -11.5	Α
Pulsed Drain Current (Notes 6 & 9)	I <sub>DM</sub>	-100	Α		
Avalanche Current (Notes 10 & 11)	I <sub>AS</sub>	-17.5	Α		
Avalanche Energy (Notes 10 & 11) L = 1mH	E <sub>AS</sub>	153	mJ		

#### Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	PD	1.26	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 5)	R <sub>0</sub> JA	97	°C/W
Power Dissipation (Note 6)	P <sub>D</sub>	2.18	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 6)	<b>R</b> θJA ▲	55	°C/W
Power Dissipation (Note 7)	$P_{D}$	14.37	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 7)	R <sub>0JA</sub>	8.7	°C/W
Power Dissipation (Notes 7 & 8)	P <sub>D</sub>	58.7	W
Thermal Resistance, Junction to Case @T <sub>C</sub> = +25°C (Notes 7 & 8)	R <sub>0JC</sub>	2.13	°C/W
Operating and Storage Temperature Range	TJ, T <sub>STG</sub>	-55 to +150	°C

### Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 11)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-30	-	_	V	$V_{GS} = 0V, I_{D} = -250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	-	<b>,</b>	-1.0	μΑ	$V_{DS} = -30V, V_{GS} = 0V$	
Gate-Source Leakage	Igss	1	l	±100	nA	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 11)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-1.1	-1.6	-2.1	V	$V_{DS} = V_{GS}$ , $I_D = -250\mu A$	
Static Drain-Source On-Resistance		<b>/</b> _	5.7	7.5	mΩ	$V_{GS} = -10V, I_{D} = -10A$	
Static Brain Godice on Resistance	R <sub>DS</sub> (ON)	_	7.2	10	11152	$V_{GS} = -4.5V$ , $I_D = -10A$	
Forward Transfer Admittance	Y <sub>fs</sub>	_	30	_	S	$V_{DS} = -15V, I_{D} = -10A$	
Diode Forward Voltage	V <sub>SD</sub>	_	-0.65	-1.0	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 12)							
Input Capacitance	Ciss	_	6,234	_	pF	V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V, f = 1.0MHz	
Output Capacitance	Coss	_	1,500	_	pF		
Reverse Transfer Capacitance	Crss	_	774	_	pF		
Gate Resistance	Rg		1.28	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = -10V)	$Q_g$		126.2	_	nC	$V_{DS} = -15V, I_{D} = -10A$	
Total Gate Charge (V <sub>GS</sub> = -4.5V)	$Q_g$		59.2	_	nC	V <sub>DS</sub> = -15V, V <sub>GS</sub> = -4.5V, -1 <sub>D</sub> = -10A	
Gate-Source Charge	$Q_{gs}$		16.1	_	nC		
Gate-Drain Charge	$Q_{gd}$	_	15.7	_	nC		
Turn-On Delay Time	t <sub>D(ON)</sub>	_	11.4	_	ns		
Turn-On Rise Time	t <sub>R</sub>	_	9.4	_	ns	$V_{DS} = -15V, V_{GEN} = -10V,$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	260.7	_	ns	$R_G = 6\Omega$ , $I_D = -1A$	
Turn-Off Fall Time	t <sub>F</sub>	_	99.3	_	ns		

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

7. Device mounted on FR-4 PCB with infinite heatsink.

8.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design. 9. Repetitive rating, pulse width limited by junction temperature, 10s pulse, duty cycle = 1%.

10.  $I_{AS}$  and  $E_{AS}$  ratings are based on low frequency and duty cycles to keep  $T_J$  = +25°C.

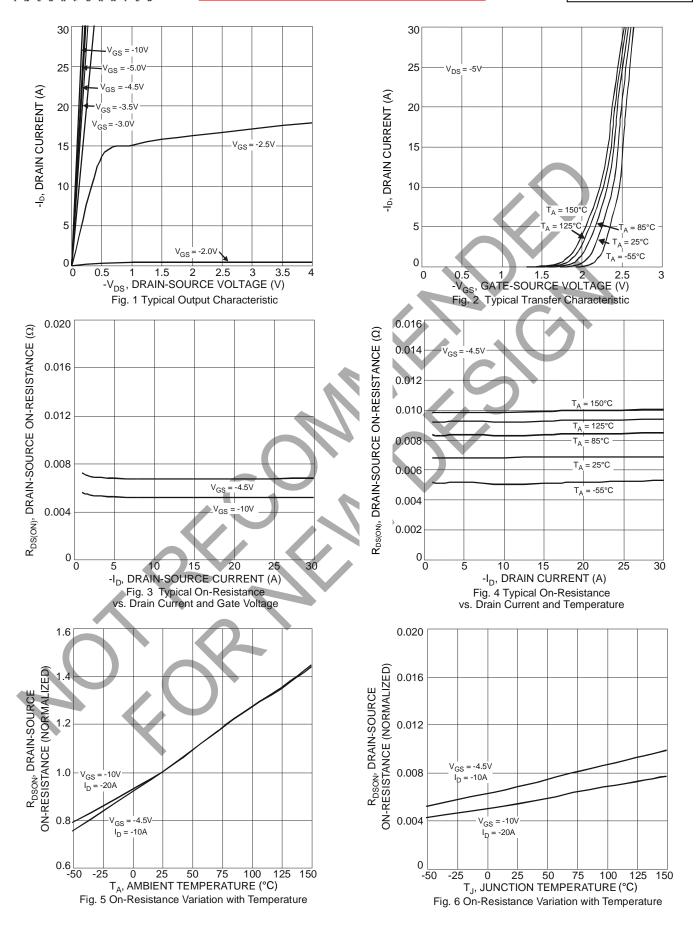
11. Short duration pulse test used to minimize self-heating effect.

12. Guaranteed by design. Not subject to product testing.



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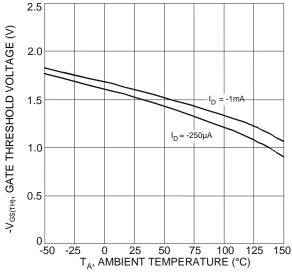
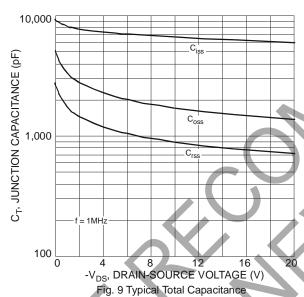
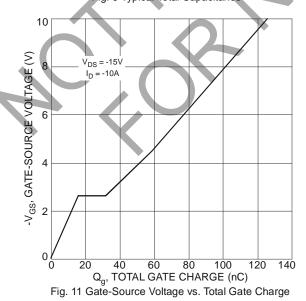
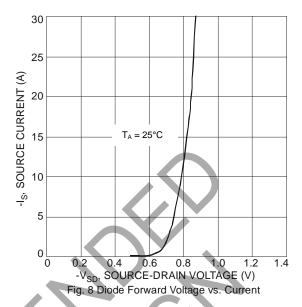


Fig. 7 Gate Threshold Variation vs. Ambient Temperature







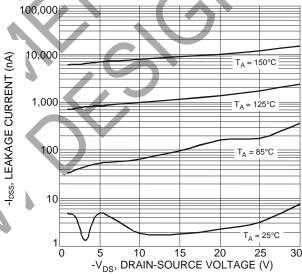
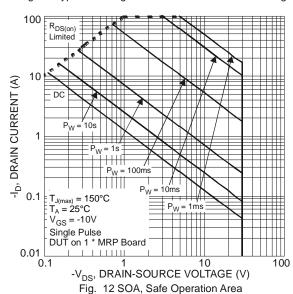


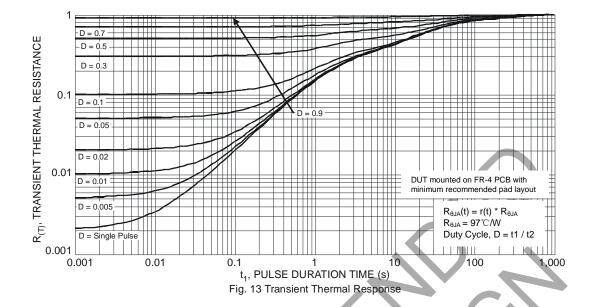
Fig. 10 Typical Leakage Current vs. Drain-Source Voltage









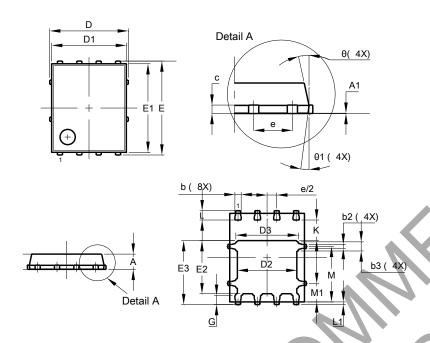




### **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8

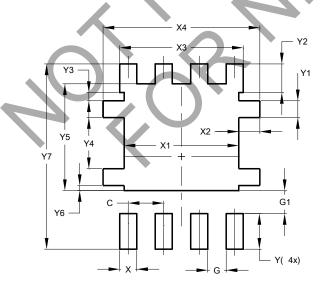


PowerDI5060-8					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0.00	0.05	-		
b	0.33	0.51	0.41		
b2	0.200	0.350	0.273		
b3	0.40	0.80	0.60		
c	0.230	0.330	0.277		
D		5.15 BSC			
D1	4.70	5.10	4.90		
D2	3.70	4.10	3.90		
D3	3.90	4.30	4.10		
Е		6.15 BSC			
E1	5.60	6.00	5.80		
<b>E2</b>	3.28	3.68	3.48		
E3	3.99	4.39	4.19		
е	1.27 BSC				
G	0.51	0.71	0.61		
K	0.51	-	-		
L	0.51	0.71	0.61		
L1	0.100	0.200	0.175		
M	3.235	4.035	3.635		
M1	1.00	1.40	1.21		
Θ	10°	12°	11°		
Θ1	6°	8°	7°		
All Dimensions in mm					

## Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

### PowerDI5060-8



Dimensions	Value (in mm)			
С	1.270			
G	0.660			
G1	0.820			
X	0.610			
X1	4.100			
X2	0.755			
Х3	4.420			
X4	5.610			
Y	1.270			
Y1	0.600			
Y2	1.020			
Y3	0.295			
Y4	1.825			
Y5	3.810			
Y6	0.180			
Y7	6.610			



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